Chennupati Jagadish

List of Publications by Year in Descending Order

862 papers	19,174 citations	64 h-index	102 g-index
1,187 ext. papers	21,922 ext. citations	5.3 avg, IF	6.65 L-index

#	Paper	IF	Citations
862	A New Strategy for Selective Area Growth of Highly Uniform InGaAs/InP Multiple Quantum Well Nanowire Arrays for Optoelectronic Device Applications (Adv. Funct. Mater. 3/2022). *Advanced Functional Materials*, **2022**, 32, 2270018	15.6	
861	Second order nonlinear frequency generation at the nanoscale in dielectric platforms. *Advances in Physics: X*, **2022**, 7,	5.1	0
860	Unique reflection from birefringent uncoated and gold-coated InP nanowire crystal arrays.. *Optics Express*, **2022**, 30, 3172-3182	3.3	1
859	III-V Semiconductor Whispering-Gallery Mode Micro-Cavity Lasers: Advances and Prospects. *IEEE Journal of Quantum Electronics*, **2022**, 1-1	2	1
858	Investigation of light-matter interaction in single vertical nanowires in ordered nanowire arrays.. *Nanoscale*, **2022**,	7.7	2
857	Protocol on the fabrication of monocrystalline thin semiconductor via crack-assisted layer exfoliation technique for photoelectrochemical water-splitting.. *STAR Protocols*, **2022**, 3, 101015	1.4	0
856	III V Compound Semiconductor Nanowire Solar Cells **2022**, 531-558		1
855	Van der Waals Heterostructures in Photocatalytic Energy Conversion **2022**, 225-274		
854	2 D- Materials-based Heterostructures for PEC Energy Conversion **2022**, 361-388		0
853	Flexible InP-ZnO nanowire heterojunction light emitting diodes.. *Nanoscale Horizons*, **2022**,	10.8	2
852	Design of InAs nanosheet arrays with ultrawide polarization-independent high absorption for infrared photodetection. *Applied Physics Letters*, **2022**, 120, 071109	3.4	1
851	Recent Advances in Materials Design Using Atomic Layer Deposition for Energy Applications. *Advanced Functional Materials*, **2022**, 32, 2109105	15.6	4
850	Self-frequency-conversion nanowire lasers.. *Light: Science and Applications*, **2022**, 11, 120	16.7	0
849	Deep-Ultraviolet Photodetectors Based on Hexagonal Boron Nitride Nanosheets Enhanced by Localized Surface Plasmon Resonance in Al Nanoparticles. *ACS Applied Nano Materials*, **2022**, 5, 7481-7491	5.6	1
848	Role of defects and grain boundaries in the thermal response of wafer-scale hBN films. *Nanotechnology*, **2021**, 32, 075702	3.4	1
847	Self-Powered InP Nanowire Photodetector for Single-Photon Level Detection at Room Temperature. *Advanced Materials*, **2021**, e2105729	24	2
846	Tunable Synthesis of 3D Niobium Oxynitride Nanosheets for Lithium-Ion Hybrid Capacitors with High Energy/Power Density. *ACS Sustainable Chemistry and Engineering*, **2021**, 9, 14569-14578	8.3	1

845	Effect of Au substrate and coating on the lasing characteristics of GaAs nanowires. *Scientific Reports*, **2021**, 11, 21378	4.9	1
844	Nanomechanical behavior of single taper-free GaAs nanowires unravelled by in-situ TEM mechanical testing and molecular dynamics simulation. *Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing*, **2021**, 806, 140866	5.3	3
843	Understanding Shape Evolution and Phase Transition in InP Nanostructures Grown by Selective Area Epitaxy. *Small*, **2021**, 17, e2100263	11	5
842	Managing Resonant and Nonresonant Lasing Modes in GaAs Nanowire Random Lasers. *Nano Letters* , **2021**, 21, 3901-3907	11.5	2
841	Fundamental Properties and Power Electronic Device Progress of Gallium Oxide **2021**, 235-352		
840	Postgrowth Shaping and Transport Anisotropy in Two-Dimensional InAs Nanofins. *ACS Nano*, **2021**, 15, 7226-7236	16.7	0
839	Ultralow Threshold, Single-Mode InGaAs/GaAs Multiquantum Disk Nanowire Lasers. *ACS Nano*, **2021**, 15, 9126-9133	16.7	3
838	Understanding, engineering, and modulating the growth of neural networks: An interdisciplinary approach. *Biophysics Reviews*, **2021**, 2, 021303	2.6	0
837	2D Carrier Localization at the Wurtzite-Zincblende Interface in Novel Layered InP Nanomembranes. *ACS Photonics*, **2021**, 8, 1735-1745	6.3	3
836	Selective area epitaxy of III–V nanostructure arrays and networks: Growth, applications, and future directions. *Applied Physics Reviews*, **2021**, 8, 021302	17.3	24
835	Epitaxially Grown InP Micro-Ring Lasers. *Nano Letters*, **2021**, 21, 5681-5688	11.5	3
834	Lasing from InP Nanowire Photonic Crystals on InP Substrate. *Advanced Optical Materials*, **2021**, 9, 2001745	8.5	4
833	Controlled Cracking for Large-Area Thin Film Exfoliation: Working Principles, Status, and Prospects. *ACS Applied Electronic Materials*, **2021**, 3, 145-162	4	5
832	Identifying carbon as the source of visible single-photon emission from hexagonal boron nitride. *Nature Materials*, **2021**, 20, 321-328	27	78
831	Understanding the role of facets and twin defects in the optical performance of GaAs nanowires for laser applications. *Nanoscale Horizons*, **2021**, 6, 559-567	10.8	3
830	Passivation of InP solar cells using large area hexagonal-BN layers. *Npj 2D Materials and Applications* , **2021**, 5,	8.8	2
829	Earth-Abundant Amorphous Electrocatalysts for Electrochemical Hydrogen Production: A Review. *Advanced Energy and Sustainability Research*, **2021**, 2, 2000071	1.6	13
828	Electron-Selective Contact for GaAs Solar Cells. *ACS Applied Energy Materials*, **2021**, 4, 1356-1364	6.1	6

827	Thin silicon via crack-assisted layer exfoliation for photoelectrochemical water splitting. *IScience*, **2021**, 24, 102921	6.1	2
826	Surface-Tailored InP Nanowires via Self-Assembled Au Nanodots for Efficient and Stable Photoelectrochemical Hydrogen Evolution. *Nano Letters*, **2021**, 21, 6967-6974	11.5	1
825	Broadband GaAsSb Nanowire Array Photodetectors for Filter-Free Multispectral Imaging. *Nano Letters*, **2021**, 21, 7388-7395	11.5	11
824	Manipulating Intermediates at the Au□TiO2 Interface over InP Nanopillar Array for Photoelectrochemical CO2 Reduction. *ACS Catalysis*, **2021**, 11, 11416-11428	13.1	7
823	Controlling the lasing modes in random lasers operating in the Anderson localization regime. *Optics Express*, **2021**, 29, 33548-33557	3.3	1
822	Spatially dense integration of micron-scale devices from multiple materials on a single chip via transfer-printing. *Optical Materials Express*, **2021**, 11, 3567	2.6	6
821	Thermodynamic properties of metastable wurtzite InP nanosheets. *Journal Physics D: Applied Physics*, **2021**, 54, 505112	3	
820	Over 17% Efficiency Stand-Alone Solar Water Splitting Enabled by Perovskite-Silicon Tandem Absorbers. *Advanced Energy Materials*, **2020**, 10, 2000772	21.8	34
819	Highly regular rosette-shaped cathodoluminescence in GaN self-assembled nanodisks and nanorods. *Nano Research*, **2020**, 13, 2500-2505	10	3
818	Polarization-Independent Indium Phosphide Nanowire Photodetectors. *Advanced Optical Materials*, **2020**, 8, 2000514	8.1	3
817	In situ passivation of GaAsSb nanowires for enhanced infrared photoresponse. *Nanotechnology*, **2020**, 31, 244002	3.4	8
816	Review on III-V Semiconductor Single Nanowire-Based Room Temperature Infrared Photodetectors. *Materials*, **2020**, 13,	3.5	17
815	Cathodoluminescence visualisation of local thickness variations of GaAs/AlGaAs quantum-well tubes on nanowires. *Nanotechnology*, **2020**, 31, 424001	3.4	2
814	Characterization, Selection, and Microassembly of Nanowire Laser Systems. *Nano Letters*, **2020**, 20, 1862-1868	11.5	12
813	Highly uniform InGaAs/InP quantum well nanowire array-based light emitting diodes. *Nano Energy*, **2020**, 71, 104576	17.1	10
812	Improving the Morphology and Crystal Quality of AlN Grown on Two-Dimensional hBN. *Crystal Growth and Design*, **2020**, 20, 1811-1819	3.5	3
811	Phase tailoring and wafer-scale uniform hetero-epitaxy of metastable-phased corundum □Ga2O3 on sapphire. *Applied Surface Science*, **2020**, 513, 145871	6.7	16
810	Strain distribution in wrinkled hBN films. *Solid State Communications*, **2020**, 310, 113847	1.6	7

809	III–V Semiconductor Materials for Solar Hydrogen Production: Status and Prospects. *ACS Energy Letters*, **2020**, 5, 611-622	20.1	33
808	Design of Ultrathin InP Solar Cell Using Carrier Selective Contacts. *IEEE Journal of Photovoltaics*, **2020**, 10, 1657-1666	3.7	9
807	Multipolar analysis of second-harmonic generation in (111) Gallium Arsenide nanoparticles. *Journal of Physics: Conference Series*, **2020**, 1461, 012185	0.3	
806	Three-dimensional cross-nanowire networks recover full terahertz state. *Science*, **2020**, 368, 510-513	33.3	36
805	Carrier dynamics and recombination mechanisms in InP twinning superlattice nanowires. *Optics Express*, **2020**, 28, 16795-16804	3.3	6
804	Non-epitaxial carrier selective contacts for III-V solar cells: A review. *Applied Materials Today*, **2020**, 18, 100503	6.6	13
803	Engineering III-V Semiconductor Nanowires for Device Applications. *Advanced Materials*, **2020**, 32, e1904359	24	19
802	Forward and Backward Switching of Nonlinear Unidirectional Emission from GaAs Nanoantennas. *ACS Nano*, **2020**, 14, 1379-1389	16.7	26
801	Monocrystalline InP Thin Films with Tunable Surface Morphology and Energy Band gap. *ACS Applied Materials & Interfaces*, **2020**, 12, 36380-36388	9.5	7
800	Solar Water Splitting: Over 17% Efficiency Stand-Alone Solar Water Splitting Enabled by Perovskite-Silicon Tandem Absorbers (Adv. Energy Mater. 28/2020). *Advanced Energy Materials*, **2020**, 10, 2070122	21.8	2
799	High-Throughput Electrical Characterization of Nanomaterials from Room to Cryogenic Temperatures. *ACS Nano*, **2020**, 14, 15293-15305	16.7	2
798	Three-Dimensional Ordered Macroporous TiO2−xNy Heterostructure for Photoelectrochemical Water Splitting. *Journal of Physical Chemistry C*, **2020**, 124, 24135-24144	3.8	3
797	Hole and Electron Effective Masses in Single InP Nanowires with a Wurtzite-Zincblende Homojunction. *ACS Nano*, **2020**, 14, 11613-11622	16.7	6
796	Impact of invasive metal probes on Hall measurements in semiconductor nanostructures. *Nanoscale* , **2020**, 12, 20317-20325	7.7	4
795	Facet-dependent growth of InAsP quantum wells in InP nanowire and nanomembrane arrays. *Nanoscale Horizons*, **2020**, 5, 1530-1537	10.8	3
794	Electrical Properties of Compact Drop-Casted Cu2SnS3 Films. *Journal of Electronic Materials*, **2020**, 49, 6403-6409	1.9	1
793	Facet-Related Non-uniform Photoluminescence in Passivated GaAs Nanowires. *Frontiers in Chemistry*, **2020**, 8, 607481	5	
792	Exploring the band structure of Wurtzite InAs nanowires using photocurrent spectroscopy. *Nano Research*, **2020**, 13, 1586-1591	10	2

791	High-Efficiency Solar Cells from Extremely Low Minority Carrier Lifetime Substrates Using Radial Junction Nanowire Architecture. *ACS Nano*, **2019**, 13, 12015-12023	16.7	18
790	Resonant harmonic generation in AlGaAs nanoantennas probed by cylindrical vector beams. *Nanoscale*, **2019**, 11, 1745-1753	7.7	16
789	Four-Dimensional Probing of Phase-Reaction Dynamics in Au/GaAs Nanowires. *Nano Letters*, **2019**, 19, 781-786	11.5	3
788	Design Principles for Fabrication of InP-Based Radial Junction Nanowire Solar Cells Using an Electron Selective Contact. *IEEE Journal of Photovoltaics*, **2019**, 9, 980-991	3.7	20
787	Introduction of TiO in CuI for Its Improved Performance as a p-Type Transparent Conductor. *ACS Applied Materials & Interfaces*, **2019**, 11, 24254-24263	9.5	14
786	Regaining a Spatial Dimension: Mechanically Transferrable Two-Dimensional InAs Nanofins Grown by Selective Area Epitaxy. *Nano Letters*, **2019**, 19, 4666-4677	11.5	16
785	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. *Scientific Reports*, **2019**, 9, 8796	4.9	18
784	InGaAsP as a Promising Narrow Band Gap Semiconductor for Photoelectrochemical Water Splitting. *ACS Applied Materials & Interfaces*, **2019**, 11, 25236-25242	9.5	14
783	Shape Engineering of InP Nanostructures by Selective Area Epitaxy. *ACS Nano*, **2019**, 13, 7261-7269	16.7	27
782	Large-Area Hexagonal Boron Nitride for Surface Enhanced Raman Spectroscopy. *Advanced Materials Technologies*, **2019**, 4, 1900220	6.8	17
781	Multiwavelength Single Nanowire InGaAs/InP Quantum Well Light-Emitting Diodes. *Nano Letters*, **2019**, 19, 3821-3829	11.5	20
780	Tailoring Second-Harmonic Emission from (111)-GaAs Nanoantennas. *Nano Letters*, **2019**, 19, 3905-3911	11.5	40
779	Compositional Varied Core-Shell InGaP Nanowires Grown by Metal-Organic Chemical Vapor Deposition. *Nano Letters*, **2019**, 19, 3782-3788	11.5	13
778	Unusual spin properties of InP wurtzite nanowires revealed by Zeeman splitting spectroscopy. *Physical Review B*, **2019**, 99,	3.3	9
777	Nanosails Showcasing Zn3As2 as an Optoelectronic-Grade Earth Abundant Semiconductor. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900084	2.5	7
776	Ultrathin TaO electron-selective contacts for high efficiency InP solar cells. *Nanoscale*, **2019**, 11, 7497-7505	7.7	28
775	Unexpected benefits of stacking faults on the electronic structure and optical emission in wurtzite GaAs/GaInP core/shell nanowires. *Nanoscale*, **2019**, 11, 9207-9215	7.7	14
774	Wavelength-tunable InAsP quantum dots in InP nanowires. *Applied Physics Letters*, **2019**, 115, 053101	3.4	4

773	Effect of Sn Addition on Epitaxial GaAs Nanowire Grown at Different Temperatures in Metal□Organic Chemical Vapor Deposition. *Crystal Growth and Design*, **2019**, 19, 5314-5319	3.5	3
772	Strong Hot Carrier Effects in Single Nanowire Heterostructures. *Nano Letters*, **2019**, 19, 5062-5069	11.5	8
771	On the origin of dislocation generation and annihilation in □Ga2O3 epilayers on sapphire. *Applied Physics Letters*, **2019**, 115, 182101	3.4	20
770	Band alignment and band bending at □Ga2O3/ZnO n-n isotype hetero-interface. *Applied Physics Letters*, **2019**, 115, 202101	3.4	13
769	Understanding the Effect of Catalyst Size on the Epitaxial Growth of Hierarchical Structured InGaP Nanowires. *Nano Letters*, **2019**, 19, 8262-8269	11.5	3
768	Nanowire Quantum Dot Surface Engineering for High Temperature Single Photon Emission. *ACS Nano*, **2019**, 13, 13492-13500	16.7	13
767	Exploiting defects in TiO inverse opal for enhanced photoelectrochemical water splitting. *Optics Express*, **2019**, 27, 761-773	3.3	27
766	Ultrasensitive Mid-wavelength Infrared Photodetection Based on a Single InAs Nanowire. *ACS Nano* , **2019**, 13, 3492-3499	16.7	28
765	Electron selective contact for high efficiency core-shell nanowire solar cell **2019**,		3
764	Engineering the Side Facets of Vertical [100] Oriented InP Nanowires for Novel Radial Heterostructures. *Nanoscale Research Letters*, **2019**, 14, 399	5	5
763	Threshold reduction and yield improvement of semiconductor nanowire lasers via processing-related end-facet optimization. *Nanoscale Advances*, **2019**, 1, 4393-4397	5.1	5
762	Axial p-n junction design and characterization for InP nanowire array solar cells. *Progress in Photovoltaics: Research and Applications*, **2019**, 27, 237-244	6.8	12
761	Solution-Processed InAs Nanowire Transistors as Microwave Switches. *Advanced Electronic Materials*, **2019**, 5, 1800323	6.4	2
760	Optical Study of p-Doping in GaAs Nanowires for Low-Threshold and High-Yield Lasing. *Nano Letters*, **2019**, 19, 362-368	11.5	17
759	Broadband Metamaterial Absorbers. *Advanced Optical Materials*, **2019**, 7, 1800995	8.1	236
758	Enhancement of radiation tolerance in GaAs/AlGaAs core-shell and InP nanowires. *Nanotechnology*, **2018**, 29, 225703	3.4	5
757	Transfer printing of semiconductor nanowire lasers. *IET Optoelectronics*, **2018**, 12, 30-35	1.5	4
756	Nonlinear Absorption Applications of CH3NH3PbBr3 Perovskite Crystals. *Advanced Functional Materials*, **2018**, 28, 1707175	15.6	63

755	Temperature effects in contacts between a metal and a semiconductor nanowire near the degenerate doping. *Nanotechnology*, **2018**,	3.4	1
754	Nonlinear Optics: Nonlinear Absorption Applications of CH3NH3PbBr3 Perovskite Crystals (Adv. Funct. Mater. 18/2018). *Advanced Functional Materials*, **2018**, 28, 1870122	15.6	3
753	Reducing Zn diffusion in single axial junction InP nanowire solar cells for improved performance. *Progress in Natural Science: Materials International*, **2018**, 28, 178-182	3.6	20
752	CdS/TiO2 photoanodes via solution ion transfer method for highly efficient solar hydrogen generation. *Nano Futures*, **2018**, 2, 015004	3.6	18
751	Indium phosphide based solar cell using ultra-thin ZnO as an electron selective layer. *Journal Physics D: Applied Physics*, **2018**, 51, 395301	3	20
750	Flow modulation epitaxy of hexagonal boron nitride. *2D Materials*, **2018**, 5, 045018	5.9	38
749	Identification and modulation of electronic band structures of single-phase □(AlxGa1□)2O3 alloys grown by laser molecular beam epitaxy. *Applied Physics Letters*, **2018**, 113, 041901	3.4	29
748	Modal refractive index measurement in nanowire lasers□ correlative approach. *Nano Futures*, **2018**, 2, 035004	3.6	5
747	Direct-coated Cu2SnS3 films from molecular solution inks for solar photovoltaics. *Materials Science in Semiconductor Processing*, **2018**, 88, 120-126	4.3	14
746	Giant optical pathlength enhancement in plasmonic thin film solar cells using core-shell nanoparticles. *Journal Physics D: Applied Physics*, **2018**, 51, 295106	3	35
745	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. *ACS Nano*, **2018**, 12, 7327-7334	16.7	7
744	Nonlinear frequency conversion in optical nanoantennas and metasurfaces: materials evolution and fabrication. *Opto-Electronic Advances*, **2018**, 1, 18002101-18002112	6.5	38
743	Distinguishing cap and core contributions to the photoconductive terahertz response of single GaAs based core□shell□ap nanowire detectors. *Lithuanian Journal of Physics*, **2018**, 58,	1.1	1
742	Tantalum Oxide Electron-Selective Heterocontacts for Silicon Photovoltaics and Photoelectrochemical Water Reduction. *ACS Energy Letters*, **2018**, 3, 125-131	20.1	83
741	Photoelectrochemical studies of InGaN/GaN MQW photoanodes. *Nanotechnology*, **2018**, 29, 045403	3.4	13
740	CuI-TiO2 Composite Thin Film for Flexible Electronic Applications **2018**,		1
739	Precise Positioning and Orientation of Nanowire Lasers in Regular and Patterned Surfaces **2018**,		2
738	Room Temperature GaAsSb Array Photodetectors **2018**,		1

737	Tuning the morphology and structure of disordered hematite photoanodes for improved water oxidation: A physical and chemical synergistic approach. *Nano Energy*, **2018**, 53, 745-752	17.1	27
736	Radial Growth Evolution of InGaAs/InP Multi-Quantum-Well Nanowires Grown by Selective-Area Metal Organic Vapor-Phase Epitaxy. *ACS Nano*, **2018**, 12, 10374-10382	16.7	18
735	Three-leaf dart-shaped single-crystal BN formation promoted by surface oxygen. *Applied Physics Letters*, **2018**, 113, 163101	3.4	
734	The effect of Sn addition on GaAs nanowire grown by vapor-liquid-solid growth mechanism. *Nanotechnology*, **2018**, 29, 465601	3.4	3
733	Vertically Emitting Indium Phosphide Nanowire Lasers. *Nano Letters*, **2018**, 18, 3414-3420	11.5	25
732	The effect of nitridation on the polarity and optical properties of GaN self-assembled nanorods. *Nanoscale*, **2018**, 10, 11205-11210	7.7	7
731	III Semiconductor Single Nanowire Solar Cells: A Review. *Advanced Materials Technologies*, **2018**, 3, 1800005	6.8	47
730	Role of surface energy in nanowire growth. *Journal Physics D: Applied Physics*, **2018**, 51, 283002	3	24
729	Perovskite Photovoltaic Integrated CdS/TiO Photoanode for Unbiased Photoelectrochemical Hydrogen Generation. *ACS Applied Materials & Interfaces*, **2018**, 10, 23766-23773	9.5	30
728	Radiation effects on GaAs/AlGaAs core/shell ensemble nanowires and nanowire infrared photodetectors. *Nanotechnology*, **2017**, 28, 125702	3.4	9
727	Single n-i-n InP nanowires for highly sensitive terahertz detection. *Nanotechnology*, **2017**, 28, 125202	3.4	14
726	Nonlinear Optical Magnetism Revealed by Second-Harmonic Generation in Nanoantennas. *Nano Letters*, **2017**, 17, 3914-3918	11.5	76
725	Engineering Highly Interconnected Neuronal Networks on Nanowire Scaffolds. *Nano Letters*, **2017**, 17, 3369-3375	11.5	43
724	Growth and optical properties of In x Ga1 P nanowires synthesized by selective-area epitaxy. *Nano Research*, **2017**, 10, 672-682	10	24
723	3D Atomic-Scale Insights into Anisotropic Core-Shell-Structured InGaAs Nanowires Grown by Metal-Organic Chemical Vapor Deposition. *Advanced Materials*, **2017**, 29, 1701888	24	13
722	The influence of surfaces on the transient terahertz conductivity and electron mobility of GaAs nanowires. *Journal Physics D: Applied Physics*, **2017**, 50, 224001	3	17
721	Strong Amplified Spontaneous Emission from High Quality GaAs1 Sbx Single Quantum Well Nanowires. *Journal of Physical Chemistry C*, **2017**, 121, 8636-8644	3.8	14
720	Improved photoelectrochemical performance of GaN nanopillar photoanodes. *Nanotechnology*, **2017**, 28, 154001	3.4	24

719	Choice of Polymer Matrix for a Fast Switchable III-V Nanowire Terahertz Modulator. *MRS Advances*, **2017**, 2, 1475-1480	0.7	1
718	An Ultrafast Switchable Terahertz Polarization Modulator Based on III-V Semiconductor Nanowires. *Nano Letters*, **2017**, 17, 2603-2610	11.5	51
717	Population dynamics and dephasing of excitons and electron-hole pairs in polytype wurtzite/zinc-blende InP nanowires. *Physical Review B*, **2017**, 95,	3.3	5
716	Hybrid Nanowire Ion-to-Electron Transducers for Integrated Bioelectronic Circuitry. *Nano Letters*, **2017**, 17, 827-833	11.5	21
715	Dopant-Free Twinning Superlattice Formation in InSb and InP Nanowires. *Physica Status Solidi - Rapid Research Letters*, **2017**, 11, 1700310	2.5	12
714	The influence of atmosphere on the performance of pure-phase WZ and ZB InAs nanowire transistors. *Nanotechnology*, **2017**, 28, 454001	3.4	12
713	Nanostructured Photoelectrodes via Template-Assisted Fabrication. *Semiconductors and Semimetals*, **2017**, 97, 289-313	0.6	2
712	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. *Scientific Reports*, **2017**, 7, 7503	4.9	10
711	Integration of Semiconductor Nanowire Lasers with Polymeric Waveguide Devices on a Mechanically Flexible Substrate. *Nano Letters*, **2017**, 17, 5990-5994	11.5	39
710	Impurity Free Vacancy Disordering (IFVD) of InGaAs/AlGaAs Quantum Well Laser Structures. *ECS Journal of Solid State Science and Technology*, **2017**, 6, N122-N126	2	
709	Large-Scale Statistics for Threshold Optimization of Optically Pumped Nanowire Lasers. *Nano Letters*, **2017**, 17, 4860-4865	11.5	23
708	A Terahertz Controlled-NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. *Advanced Optical Materials*, **2017**, 5, 1700108	8.1	8
707	InP-InGaAs core-multi-shell nanowire quantum wells with tunable emission in the 1.3-1.55 μm wavelength range. *Nanoscale*, **2017**, 9, 13554-13562	7.7	8
706	Engineering the Photoresponse of InAs Nanowires. *ACS Applied Materials & Interfaces*, **2017**, 9, 43993-44000	8.5	34
705	Dynamics and control of gold-encapped gallium arsenide nanowires imaged by 4D electron microscopy. *Proceedings of the National Academy of Sciences of the United States of America*, **2017**, 114, 12876-12881	11.5	12
704	Critical Temperature for the Conversion from Wurtzite to Zincblende of the Optical Emission of InAs Nanowires. *Journal of Physical Chemistry C*, **2017**, 121, 16650-16656	3.8	0
703	Excited State Biexcitons in Atomically Thin MoSe. *ACS Nano*, **2017**, 11, 7468-7475	16.7	44
702	Tunable Photoresponse in InAs Nanowire Photodetectors Through Surface-State Engineering **2017**,		1

701	Spontaneous formation of core-shell GaAsP nanowires with enhanced electrical conductivity **2016**, 463-465		
700	Bandgap Energy of Wurtzite InAs Nanowires. *Nano Letters*, **2016**, 16, 5197-203	11.5	37
699	Temperature-dependent side-facets of GaAs nanopillars. *Semiconductor Science and Technology*, **2016**, 31, 094004	1.8	3
698	High-Brightness Polarized Green InGaN/GaN Light-Emitting Diode Structure with Al-Coated p-GaN Grating. *ACS Photonics*, **2016**, 3, 1912-1918	6.3	20
697	Review on photonic properties of nanowires for photovoltaics. *Optics Express*, **2016**, 24, 17345-58	3.3	32
696	Nonconservative dynamics of optically trapped high-aspect-ratio nanowires. *Physical Review E*, **2016**, 93, 022137	2.4	11
695	Broadband Phase-Sensitive Single InP Nanowire Photoconductive Terahertz Detectors. *Nano Letters*, **2016**, 16, 4925-31	11.5	27
694	Design and fabrication of silicon nanowires towards efficient solar cells. *Nano Today*, **2016**, 11, 704-737	17.9	129
693	Nonlinear Generation of Vector Beams From AlGaAs Nanoantennas. *Nano Letters*, **2016**, 16, 7191-7197	11.5	168
692	Doping-enhanced radiative efficiency enables lasing in unpassivated GaAs nanowires. *Nature Communications*, **2016**, 7, 11927	17.4	57
691	Simultaneous Selective-Area and Vapor-Liquid-Solid Growth of InP Nanowire Arrays. *Nano Letters*, **2016**, 16, 4361-7	11.5	46
690	Growth of Catalyst-Free Epitaxial InAs Nanowires on Si Wafers Using Metallic Masks. *Nano Letters*, **2016**, 16, 4189-93	11.5	9
689	Enhanced luminescence from GaN nanopillar arrays fabricated using a top-down process. *Nanotechnology*, **2016**, 27, 065304	3.4	19
688	Thermal Delocalization of Excitons in GaAs/AlGaAs Quantum Well Tube Nanowires. *Nano Letters*, **2016**, 16, 1392-7	11.5	6
687	Transfer Printing of Semiconductor Nanowires with Lasing Emission for Controllable Nanophotonic Device Fabrication. *ACS Nano*, **2016**, 10, 3951-8	16.7	36
686	Effect of a High Density of Stacking Faults on the Young's Modulus of GaAs Nanowires. *Nano Letters*, **2016**, 16, 1911-6	11.5	48
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